Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	10/656,432	US-PGPUB; USPAT	OR	OFF	2006/02/13 13:45
L2	6059	((250/299,292,282,288,) or (216/2,) or (313/326,)).CCLS.	USPAT; USOCR	OR	OFF	2006/02/13 13:47
L3	679	2 and (fabric$5 near4 semiconductor or wafer)	USPAT	OR	OFF	2006/02/13 13:53
L4	13	3 and (fabric$5 near4 dielectric)	USPAT	OR	OFF	2006/02/13 13:56
L5	10	3 and (etch near4 electrode)	USPAT	OR	OFF	2006/02/13 13:48
L6	72	3 and (form near4 electrode)	USPAT	OR	OFF	2006/02/13 13:48
L7	3	6 and (fabric$5 near4 dielectric)	USPAT	OR	OFF	2006/02/13 13:58
L8	0	6 and (akternate near4 layers)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/13 13:50
L9	0	6 and (alternate near4 layers)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/13 13:50
L10	5	3 and (alternate near4 layers)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/13 13:50
L11	731	2 and (fabric$5 near4 semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 13:56
L12	13	11 and (fabric$5 near4 dielectric)	USPAT	OR	OFF	2006/02/13 13:57
L13	13	11 and (fabric$5 near4 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/13 13:57
L14	13	11 and (fabric$5 near4 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/13 13:58

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L15	0	(fabric$5 near4 semiconductor or wafer) and (fabric$5 near5 dielctric)and (alternate near4 layers) and (conductove near4 layer) and (hole near4 cavity).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/13 14:00
L16	0	(fabric$5 near4 semiconductor or wafer) and (fabric$5 near5 dielctric)and (alternate near4 layers) and (conductove near4 layer) and (hole near4 cavity).clm.	US-PGPUB; USPAT	OR	ON	2006/02/13 14:01
L17	5	(pai-chien-shing) and (pau-stanley). IN.	US-PGPUB; USPAT	OR	ON	2006/02/13 14:01